AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

LISTING OF CLAIMS:

1.-10. (Canceled)

11. (Currently Amended) A silicon carbide component ~~of~~ for a semiconductor substrate processing apparatus, the silicon carbide component being porous and comprising an interior and an exposed surface, the silicon carbide component having been (i) made by a ~~carbon~~ graphite conversion process that results in the silicon carbide component including free-carbon in graphite form in the interior; (ii) treated to produce an exposed surface having the free-carbon in graphite form therein; and (iii) treated to remove the free-carbon such that at least the exposed surface is substantially free of the free-carbon, wherein the silicon carbide component is selected from the group consisting of a baffle plate, a plasma confinement ring and an edge ring.

12. (Previously Presented) The silicon carbide component of Claim 11, wherein the silicon carbide component is a baffle plate.

13. (Original) A semiconductor substrate processing apparatus comprising a plasma processing chamber and at least one silicon carbide component according to Claim 11 in the plasma processing chamber.

14. (Original) The semiconductor substrate processing apparatus of Claim 13, wherein the plasma processing chamber is an etching chamber.

15.-28. (Canceled)

29. (Currently Amended) The silicon carbide component of Claim 11, wherein the silicon carbide component ~~is a new component~~ has been treated and has not been installed in the semiconductor substrate processing apparatus.

30. (Currently Amended) The silicon carbide component of Claim 11, wherein the silicon carbide component has ~~not~~ been ~~exposed to plasma~~ treated in [[a]] an oxygen-containing atmosphere in a treatment vessel and has not been installed in the semiconductor substrate processing apparatus.

31. (Currently Amended) ~~The silicon carbide component of Claim 11, wherein the silicon carbide component has not been exposed to plasma processing during the processing of production semiconductor substrates in a semiconductor substrate processing apparatus.~~

A semiconductor substrate processing apparatus comprising the silicon carbide component according to Claim 11.

32. (Currently Amended) The silicon carbide component of Claim 11, wherein the ~~free-carbon~~ graphite comprises ~~carbon~~ graphite clusters having a size of about 20 μm to about 200 μm.

33. (Currently Amended) The silicon carbide component of Claim 11, wherein the exposed surface is a machined surface substantially free of the free-carbon and the interior of the silicon carbide component contains free-carbon in graphite form.

34. (Previously Presented) The silicon carbide component of Claim 11, wherein the silicon carbide component has a thickness of up to about ¼ inch.

35. (Currently Amended) A silicon carbide component ~~of~~ for a semiconductor substrate processing apparatus, the silicon carbide component comprising an interior and an exposed surface, the interior containing free-carbon in graphite form and the exposed surface being substantially free of the free-carbon, wherein the silicon carbide component is selected from the group consisting of a baffle plate, a plasma confinement ring and an edge ring.

36. (Previously Presented) The silicon carbide component of Claim 35, wherein the silicon carbide component is a baffle plate

37. (Currently Amended) The silicon carbide component of Claim 35, wherein the silicon carbide component ~~is a new component~~ has been treated and has not been installed in the semiconductor substrate processing apparatus.

38. (Currently Amended) The silicon carbide component of Claim 35, wherein the silicon carbide component has ~~not~~ been ~~exposed to plasma~~ treated in [[a]] an oxygen-containing atmosphere in a treatment vessel and has not been installed in the semiconductor substrate processing apparatus.

39. (Currently Amended) ~~The silicon carbide component of Claim 35, wherein the silicon carbide component has not been exposed to plasma during the processing of production semiconductor substrates in a semiconductor substrate processing apparatus.~~

A semiconductor substrate processing apparatus comprising the silicon carbide component according to Claim 35.

40. (Currently Amended) The silicon carbide component of Claim 35, wherein the ~~free-carbon~~ graphite comprises ~~carbon~~ graphite clusters having a size of about 20 μm to about 200 μm.

41. (Currently Amended) The silicon carbide component of Claim 35, wherein the exposed surface is a machined surface substantially free of the free-carbon and the interior of the silicon carbide component contains the free-carbon.

42. (Previously Presented) The silicon carbide component of Claim 35, wherein the silicon carbide component has a thickness of up to about ¼ inch.

43. (Currently Amended) A silicon carbide baffle plate ~~of~~ for a semiconductor substrate processing apparatus, the baffle plate comprising an interior and a machined exposed surface, the interior containing free-carbon particles or clusters in graphite form and the exposed surface being substantially free of the free-carbon.

44. (Currently Amended) The silicon carbide baffle plate of Claim 43, wherein the silicon carbide component ~~is a new component~~ has been treated and has not been installed in the semiconductor substrate processing apparatus.